

# **TF212**

Preliminary

# **CAPACITOR MICROPHONE APPLICATIONS**

#### DESCRIPTION

The UTC TF212 uses advanced trench technology to provide excellent R<sub>DS (ON)</sub>, low gate charge and operation with low gate voltages. This device is suitable for use in capacitor microphone applications.

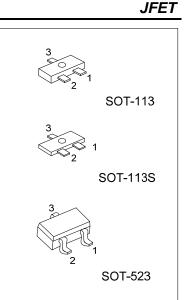
#### **FEATURES**

\* Suited for use in audio, telephone capacitor microphones.

- \* Good voltage characteristic.
- \* Good transient characteristic.

\* Halogen Free

## **ORDERING INFORMATION**



Ordering Number	Package	Pin Assignment			Docking	
Ordering Number		1	2	3	Packing	
TF212G-x-AC3-R	SOT-113	S	D	G	Tape Reel	
TF212G-x-A3C-R	SOT-113S	S	D	G	Tape Reel	
TF212G-x-AN3-R	SOT-523	S	D	G	Tape Reel	

TF212 <u>G-x-AC3-R</u>	(1)Packing Type (2)Package Type (3)Rank	<ul> <li>(1) R: Tape Reel</li> <li>(2) AC3: SOT-113, A3C: SOT-113S, AN3: SOT-523</li> <li>(3) x: refer to Classification of I<sub>DSS</sub></li> </ul>
	(3)Rank (4)Halogen Free	(4) G: Halogen Free

# MARKING

TF212-F4	TF212-F5		
	<u>B</u> _		
F4	F5		

### ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Gate Drain Voltage	V <sub>GDO</sub>	-20	V
Gate Current	l <sub>G</sub>	10	mA
Drain Current	ID	1	mA
Power Dissipation	PD	100	mW
Junction Temperature	TJ	150	°C
Storage Temperature	T <sub>STG</sub>	-55~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

#### ■ ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

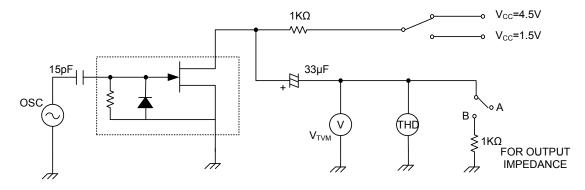
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Gate Drain Breakdown Voltage	BV <sub>GDO</sub>	I <sub>G</sub> =-100μA	-20			V
Gate Source Cut off Voltage	V <sub>GS(OFF)</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =1µA	-0.2	-0.6	-1.2	V
Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =5V, V <sub>GS</sub> =0	140		350	μA
Forward Transfer Admittance	IYFSI	V <sub>DS</sub> =2V, V <sub>GS</sub> =0, f=1KHz	1	1.2		mS
Input Capacitance	CISS	V <sub>DS</sub> =5V, V <sub>GS</sub> =0, f=1MHz		3.5		pF
Output Capacitance	C <sub>RSS</sub>	V <sub>DS</sub> =5V, V <sub>GS</sub> =0, f=1MHz		0.65		pF
Voltage Gain	Gv	V <sub>IN</sub> =10mV, f=1KHz		-3		dB
Reduced Voltage Characteristic	∆Gvv	V <sub>IN</sub> =10mV,f=1KHz, V <sub>CC</sub> =4.5V→1.5V		-1.2	-3.5	dB
Frequency Characteristic	∆G <sub>Vf</sub>	f=1KHz to 110Hz			-1	dB
Input Resistance	Z <sub>IN</sub>	f=1KHz	25			MΩ
Output Resistance	Zo	f=1KHz			700	Ω
Total Harmonic distortion	THD	V <sub>IN</sub> =30mV, f=1KHz		1		%
Output Noise Voltage	V <sub>NO</sub>	V <sub>IN</sub> =0			-110	dB

# ■ CLASSIFICATION OF I<sub>DSS</sub>

RANK	F4	F5
RANGE	140-240	210-350



### ■ TEST CIRCUIT (Ta=25°C)



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